

### Features

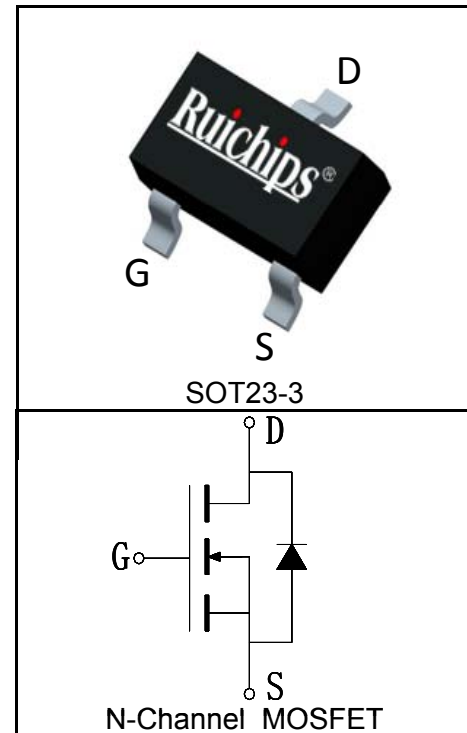
- 30V/6A,  
 $R_{DS(ON)} = 18m\Omega(Typ.)@V_{GS}=10V$   
 $R_{DS(ON)} = 28m\Omega(Typ.)@V_{GS}=4.5V$
- Low  $R_{DS(ON)}$
- Super High Dense Cell Design
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)



### Applications

- Load Switch
- Power Management
- Battery Protection

### Pin Description



### Absolute Maximum Ratings

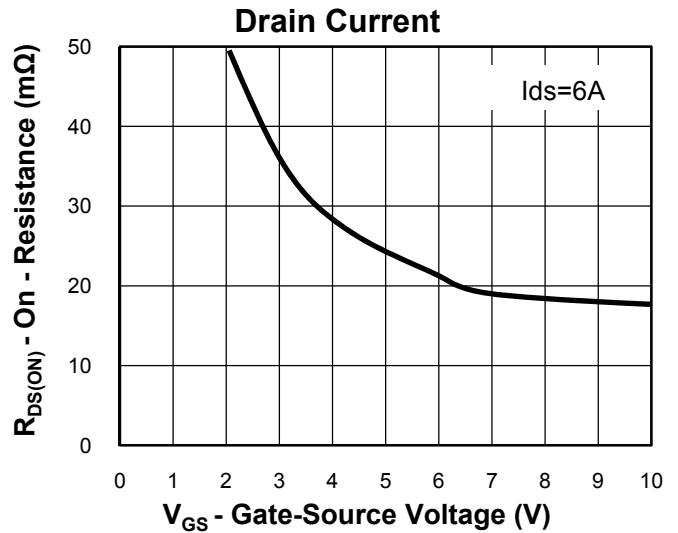
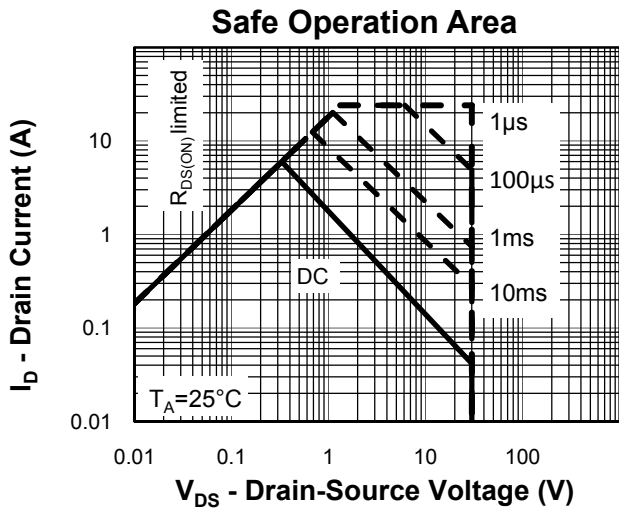
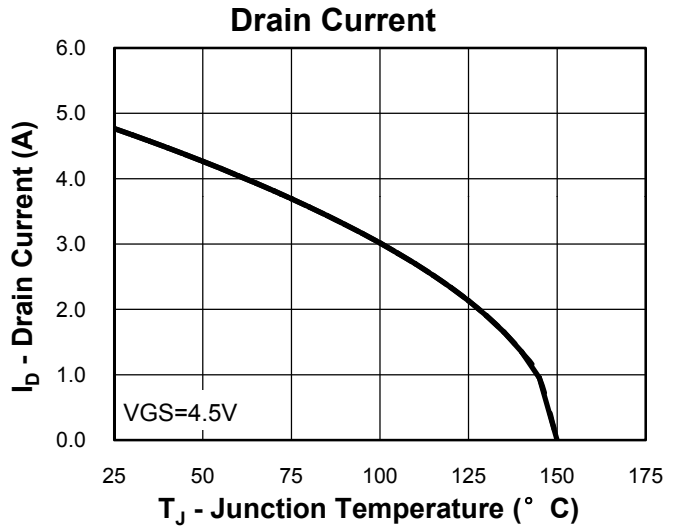
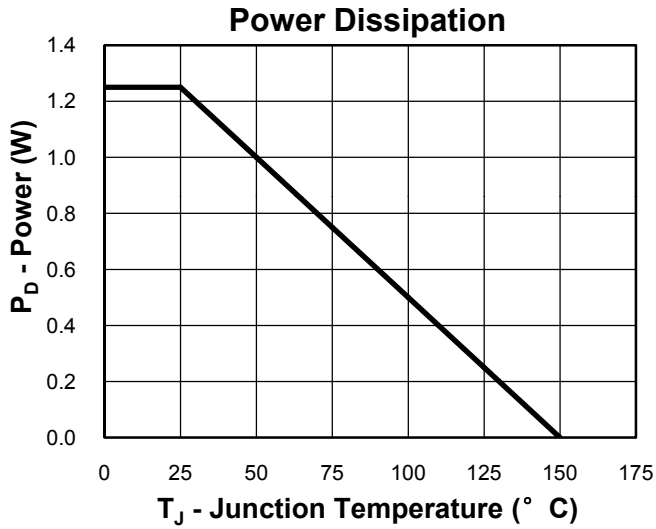
| Symbol   | Parameter                                | Rating                   | Unit         |
|--|--|--------------------------|--------------|
| <b>Common Ratings</b> ( $T_A=25^\circ C$ Unless Otherwise Noted) |  |                          |              |
| $V_{DSS}$  | Drain-Source Voltage                     | 30                       | V            |
| $V_{GSS}$  | Gate-Source Voltage                      | $\pm 12$                 |              |
| $T_J$  | Maximum Junction Temperature             | 150                      | $^\circ C$   |
| $T_{STG}$  | Storage Temperature Range                | -55 to 150               | $^\circ C$   |
| $I_S$  | Diode Continuous Forward Current         | $T_A=25^\circ C$<br>1    | A            |
| <b>Mounted on Large Heat Sink</b>                                |  |                          |              |
| $I_{DP}^{①}$   | 300 $\mu s$ Pulse Drain Current Tested   | $T_A=25^\circ C$<br>24   | A            |
| $I_D^{②}$  | Continuous Drain Current( $V_{GS}=10V$ ) | $T_A=25^\circ C$<br>6    | A            |
|  |  | $T_A=70^\circ C$<br>4.5  |              |
| $P_D$  | Maximum Power Dissipation                | $T_A=25^\circ C$<br>1.25 | W            |
|  |  | $T_A=70^\circ C$<br>0.75 |              |
| $R_{\theta JC}$  | Thermal Resistance-Junction to Case      | -                        | $^\circ C/W$ |
| $R_{\theta JA}^{③}$  | Thermal Resistance-Junction to Ambient   | 100                      | $^\circ C/W$ |
| <b>Drain-Source Avalanche Ratings</b>                            |  |                          |              |
| $E_{AS}^{④}$   | Avalanche Energy, Single Pulsed          | TBD                      | mJ           |

**Electrical Characteristics** ( $T_A=25^\circ\text{C}$  Unless Otherwise Noted)

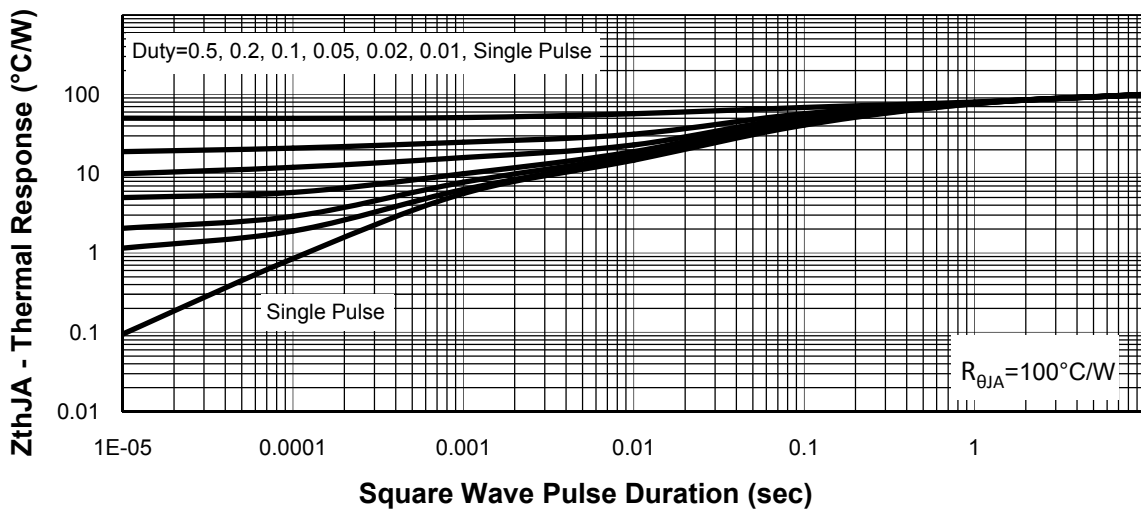
| Symbol  | Parameter                        | Test Condition   | RU307C |      |           | Unit      |
|---|----------------------------------|--|--------|------|-----------|-----------|
|   |                                  |  | Min.   | Typ. | Max.      |           |
| <b>Static Characteristics</b>                     |                                  |  |        |      |           |           |
| $BV_{DSS}$  | Drain-Source Breakdown Voltage   | $V_{GS}=0V, I_{DS}=250\mu A$                             | 30     |      |           | V         |
| $I_{DSS}$   | Zero Gate Voltage Drain Current  | $V_{DS}=30V, V_{GS}=0V$                                  |        |      | 1         | $\mu A$   |
|   |                                  | $T_J=125^\circ\text{C}$                                  |        |      | 30        |           |
| $V_{GS(th)}$                                      | Gate Threshold Voltage           | $V_{DS}=V_{GS}, I_{DS}=250\mu A$                         | 0.7    | 1    | 1.8       | V         |
| $I_{GSS}$   | Gate Leakage Current             | $V_{GS}=\pm 12V, V_{DS}=0V$                              |        |      | $\pm 100$ | nA        |
| $R_{DS(ON)}^{(5)}$                                | Drain-Source On-state Resistance | $V_{GS}=10V, I_{DS}=6A$                                  |        | 18   | 25        | $m\Omega$ |
|   |                                  | $V_{GS}=4.5V, I_{DS}=5A$                                 |        | 28   | 35        | $m\Omega$ |
| <b>Diode Characteristics</b>                      |                                  |  |        |      |           |           |
| $V_{SD}^{(5)}$                                    | Diode Forward Voltage            | $I_{SD}=1A, V_{GS}=0V$                                   |        |      | 1         | V         |
| $t_{rr}$  | Reverse Recovery Time            | $I_{SD}=1A, di_{SD}/dt=100A/\mu s$                       |        | 17   |           | ns        |
| $Q_{rr}$  | Reverse Recovery Charge          |  |        | 8    |           | nC        |
| <b>Dynamic Characteristics</b> <sup>(6)</sup>     |                                  |  |        |      |           |           |
| $R_G$   | Gate Resistance                  | $V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$                    |        | 1.5  |           | $\Omega$  |
| $C_{iss}$   | Input Capacitance                | $V_{GS}=0V,$<br>$V_{DS}=15V,$<br>Frequency=1.0MHz        |        | 610  |           | pF        |
| $C_{oss}$   | Output Capacitance               |  |        | 130  |           |           |
| $C_{rss}$   | Reverse Transfer Capacitance     |  |        | 90   |           |           |
| $t_{d(ON)}$                                       | Turn-on Delay Time               | $V_{DD}=15V, I_{DS}=6A,$<br>$V_{GEN}=10V, R_G=4.7\Omega$ |        | 9    |           | ns        |
| $t_r$   | Turn-on Rise Time                |  |        | 16   |           |           |
| $t_{d(OFF)}$                                      | Turn-off Delay Time              |  |        | 34   |           |           |
| $t_f$   | Turn-off Fall Time               |  |        | 13   |           |           |
| <b>Gate Charge Characteristics</b> <sup>(6)</sup> |                                  |  |        |      |           |           |
| $Q_g$   | Total Gate Charge                | $V_{DS}=24V, V_{GS}=10V,$<br>$I_{DS}=6A$                 |        | 12   |           | nC        |
| $Q_{gs}$  | Gate-Source Charge               |  |        | 1.9  |           |           |
| $Q_{gd}$  | Gate-Drain Charge                |  |        | 3.7  |           |           |

- Notes:
- ① Pulse width limited by safe operating area.
  - ② Calculated continuous current based on maximum allowable junction temperature.
  - ③ When mounted on 1 inch square copper board,  $t \leq 10\text{sec}$ . The value in any given application depends on the user's specific board design.
  - ④ Limited by  $T_{Jmax}$ . Starting  $T_J = 25^\circ\text{C}$ .
  - ⑤ Pulse test; Pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
  - ⑥ Guaranteed by design, not subject to production testing.

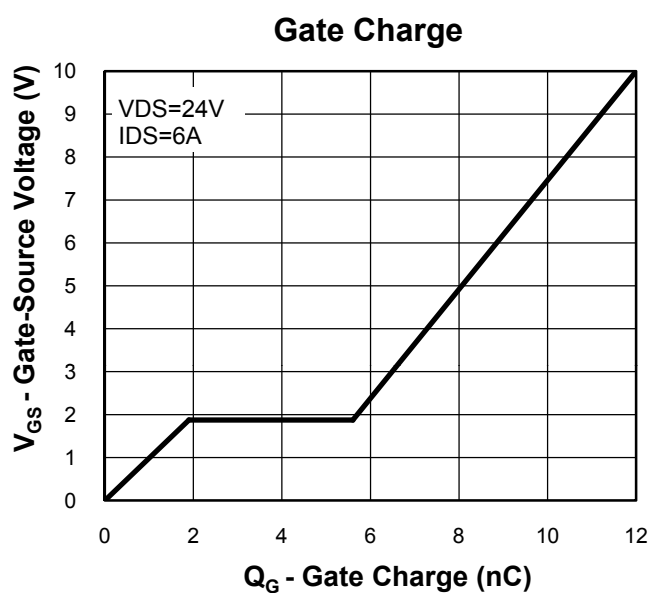
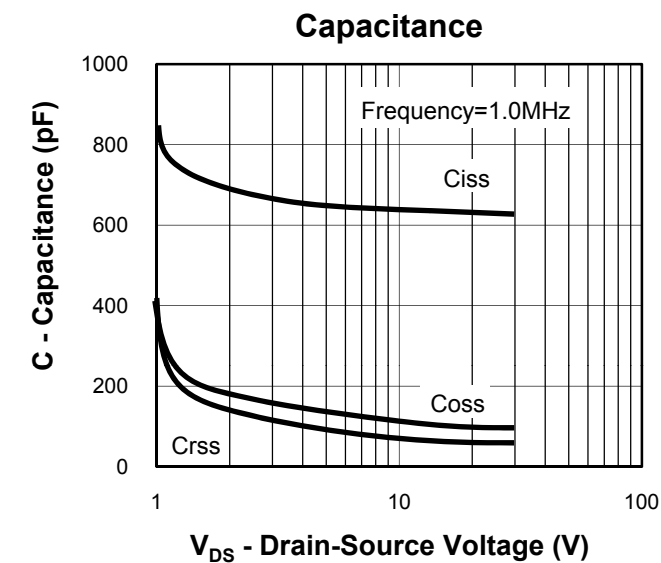
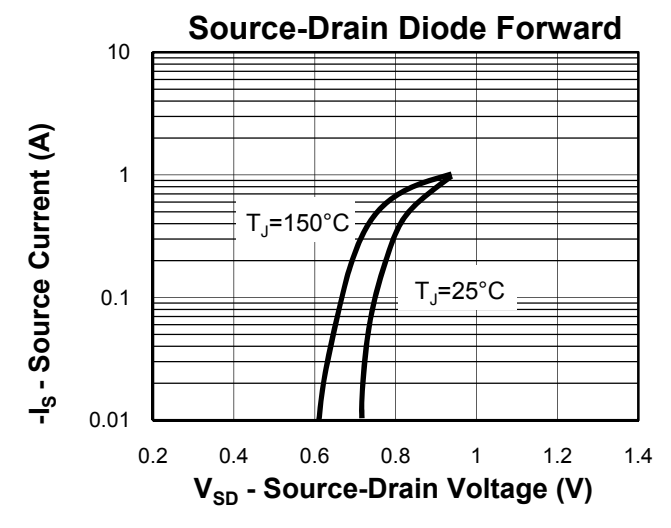
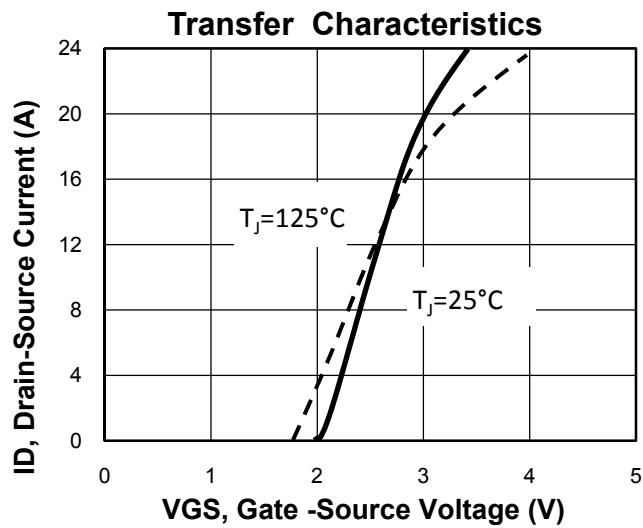
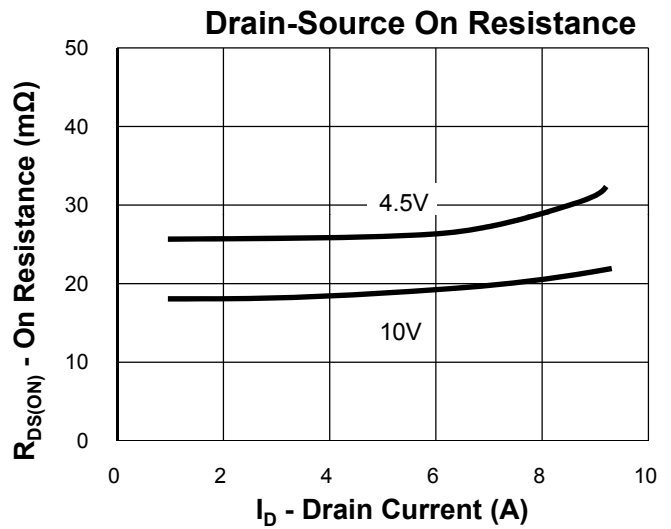
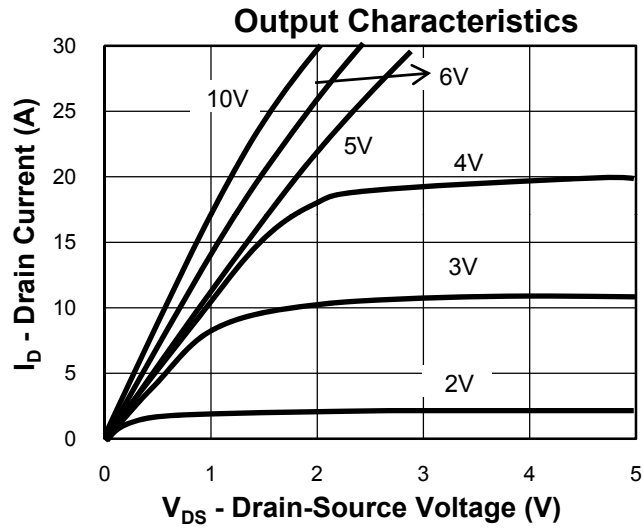
**Typical Characteristics**



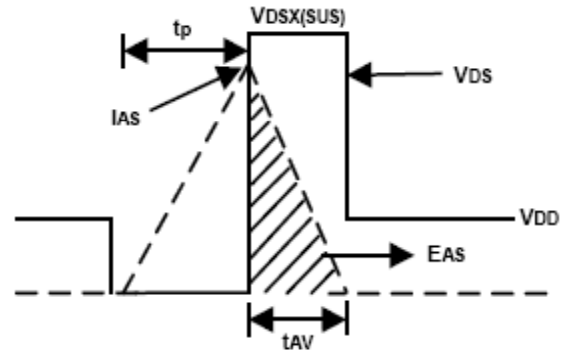
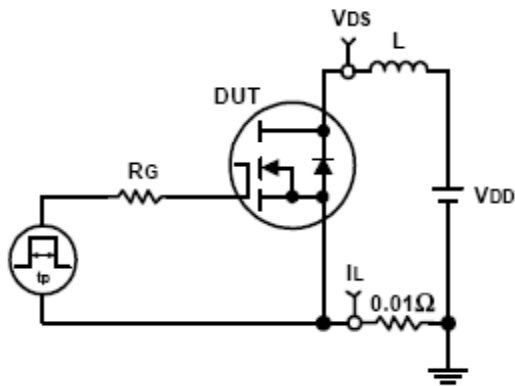
**Thermal Transient Impedance**



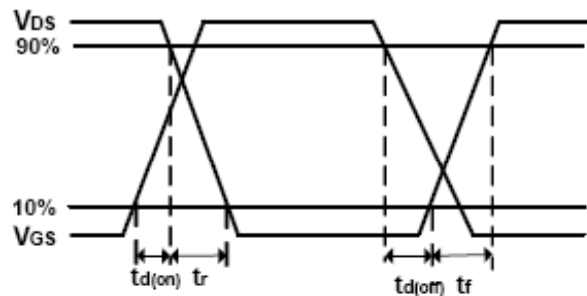
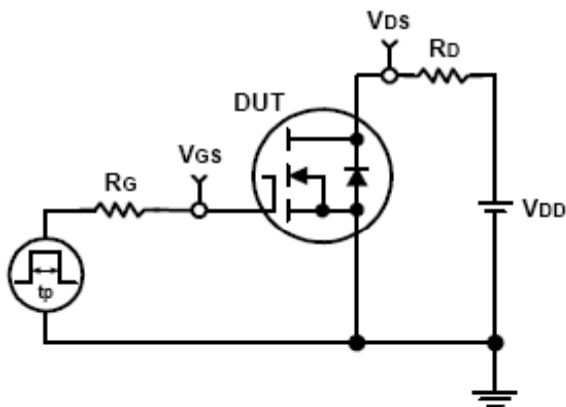
**Typical Characteristics**



**Avalanche Test Circuit and Waveforms**



**Switching Time Test Circuit and Waveforms**

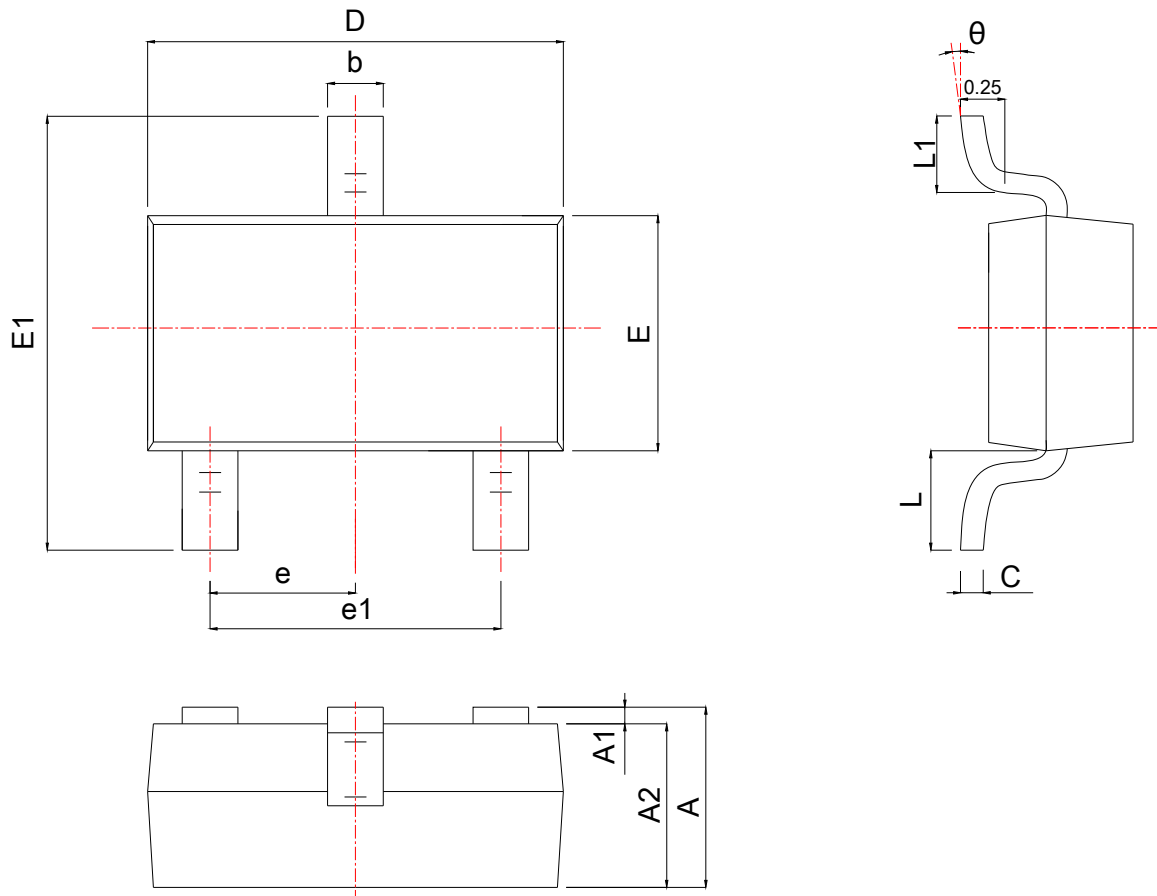


**Ordering and Marking Information**

| Device | Marking | Package | Packaging | Quantity | Reel Size | Tape width |
|--------|---------|---------|-----------|----------|-----------|------------|
| RU307C | RU307   | SOT23-3 | Tape&Reel | 3000     | 7"        | 8mm        |

**Package Information**

**SOT23-3**



| SYMBOL | MM        |       |       | INCH      |       |       |
|--------|-----------|-------|-------|-----------|-------|-------|
|        | MIN       | NOM   | MAX   | MIN       | NOM   | MAX   |
| A      | 0.950     | 1.150 | 1.450 | 0.037     | 0.045 | 0.057 |
| A1     | 0.000     | *     | 0.150 | 0.000     | *     | 0.006 |
| A2     | 0.900     | 1.100 | 1.300 | 0.035     | 0.043 | 0.051 |
| b      | 0.300     | 0.400 | 0.500 | 0.012     | 0.016 | 0.020 |
| c      | 0.080     | 0.150 | 0.200 | 0.003     | 0.006 | 0.008 |
| D      | 2.800     | 2.925 | 3.050 | 0.110     | 0.115 | 0.120 |
| E      | 1.500     | 1.600 | 1.750 | 0.059     | 0.063 | 0.069 |
| E1     | 2.650     | 2.800 | 3.000 | 0.104     | 0.110 | 0.118 |
| e      | 0.950 BSC |       |       | 0.037 BSC |       |       |
| e1     | 1.800     | 1.900 | 2.000 | 0.071     | 0.075 | 0.079 |
| L      | 0.300     | 0.450 | 0.600 | 0.012     | 0.018 | 0.024 |
| θ      | 0°        | 4°    | 8°    | 0°        | 4°    | 8°    |

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